DATA SHEET



16M-BIT MASK-PROGRAMMABLE ROM 2M-WORD BY 8-BIT (BYTE MODE) / 1M-WORD BY 16-BIT (WORD MODE) PAGE ACCESS MODE

Description

The μ PD23C16340 and μ PD23C16380 are 16,777,216 bits mask-programmable ROM. The word organization is selectable (BYTE mode : 2,097,152 words by 8 bits, WORD mode : 1,048,576 words by 16 bits).

The active levels of OE (Output Enable Input) can be selected with mask-option.

The μ PD23C16340 and μ PD23C16380 are packed in 48-pin PLASTIC TSOP(I) and 48-pin TAPE FBGA.

Features

- Pin compatible with NOR Flash Memory
- Word organization

2,097,152 words by 8 bits (BYTE mode)

1,048,576 words by 16 bits (WORD mode)

Page access mode

BYTE mode : 8 byte random page access (µPD23C16340)

16 byte random page access (µPD23C16380)

WORD mode : 4 word random page access (µPD23C16340)

8 word random page access (µPD23C16380)

• Operating supply voltage : Vcc = 2.7 V to 3.6 V

Operating supply	Access time /	Power supply current (Active mode)		Standby current
voltage	Page access time	mA (MAX.)		(CMOS level input)
Vcc	ns (MAX.)	μPD23C16340	μPD23C16380	μΑ (MAX.)
$3.0~V\pm0.3~V$	90 / 25	40	55	30
$3.3~V\pm0.3~V$	85 / 25			

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μPD23C16340, 23C16380

Ordering Information

Part Number	Package
μPD23C16340GZ-xxx-MJH	48-pin PLASTIC TSOP(I) (12 x 20) (Normal bent)
μPD23C16340F9-xxx-BC3	48-pin TAPE FBGA (8 x 6)
μPD23C16380GZ-xxx-MJH	48-pin PLASTIC TSOP(I) (12 x 20) (Normal bent)
μPD23C16380F9-xxx-BC3	48-pin TAPE FBGA (8 x 6)

(xxx : ROM code suffix No.)

Data Sheet M15709EJ2V0DS

Pin Configurations

/xxx indicates active low signal.

48-pin PLASTIC TSOP(I) (12 x 20) (Normal bent)

[µPD23C16340GZ-xxx-MJH]

[µPD23C16380GZ-xxx-MJH]

	Marking Side	
A15 O	1 48	
A14 O	2 47	
A13 0	3 46	
A12 O	4 45	 →○ 015, A–1
A11 0	5 44	
A10 O	6 43	
	7 42	
A8 O	8 41	
A19 O	9 40	
	10 39	
	11 38	
	12 37	
	13 36	
	14 35	
	15 34	
A18 O	16 33	-0 02
A10 0 -	17 32	
AT 0	18 31	
A6 O	19 30	-0 08
A5 O	20 29	
AJ ()	21 28	 OU O
	22 27 27	
A3 O		
A2 O		
A1 O──►	24 25	

A0 to A19	:	Address inputs
O0 to O7, O8 to O14		Data outputs
O15, A–1	:	Data output 15 (WORD mode),
		LSB Address input (BYTE mode)
WORD, /BYTE	:	Mode select
/CE	:	Chip Enable
/OE or OE	:	Output Enable
Vcc	:	Supply voltage
GND	:	Ground
NC Note	:	No Connection
DC	:	Don't Care

Note Some signals can be applied because this pin is not connected to the inside of the chip.

Remark Refer to Package Drawings for the 1-pin index mark.

Data Sheet M15709EJ2V0DS

48-pin TAPE FBGA (8 x 6)

[µPD23C16340F9-xxx-BC3]

[µPD23C16380F9-xxx-BC3]

Top View				

ABCDEFGH

	А	В	С	D	Е	F	G	Н
6	A13	A12	A14	A15	A16	WORD,	O15,	GND
						/BYTE	A–1	
5	A9	A8	A10	A11	07	O14	O13	O6
4	NC	NC	NC	A19	O5	O12	Vcc	04
3	NC	NC	A18	NC	O2	O10	011	O3
2	A7	A17	A6	A5	00	O8	O9	01
1	A3	A4	A2	A1	A0	/CE	/OE or	GND
							OE	

	н	G	F	Е	D	С	в	А	
	0	0	0	0	0	0	0	0	
	\bigcirc								
00000000	\bigcirc								
	\bigcirc								
00000000	\bigcirc								
	0	0	0	0	\bigcirc	0	\bigcirc	\bigcirc	

Bottom View

	Н	G	F	Е	D	С	В	А
6	GND	O15,	WORD,	A16	A15	A14	A12	A13
		A–1	/BYTE					
5	O6	O13	O14	07	A11	A10	A8	A9
4	O4	Vcc	O12	O5	A19	NC	NC	NC
3	O3	011	O10	O2	NC	A18	NC	NC
2	01	O9	O8	O0	A5	A6	A17	A7
1	GND	/OE or	/CE	A0	A1	A2	A4	A3
		OE						

A0 to A19	:	Address inputs
O0 to O7, O8 to O14	:	Data outputs
O15, A–1	:	Data output 15 (WORD mode),
		LSB Address input (BYTE mode)
WORD, /BYTE	:	Mode select
/CE	:	Chip Enable
/OE or OE	:	Output Enable
Vcc	:	Supply voltage
GND	:	Ground
NC Note	:	No Connection
DC	:	Don't Care

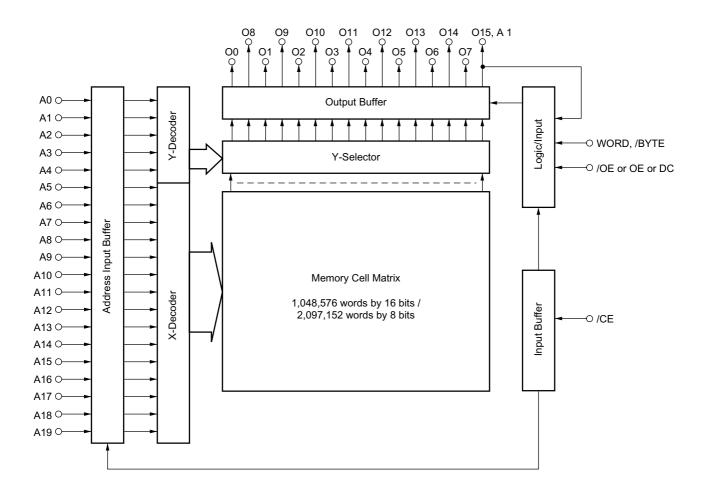
Note Some signals can be applied because this pin is not connected to the inside of the chip.

Remark Refer to Package Drawings for the index mark.

Input / Output Pin Functions

Pin name	Input / Output	Function	
WORD, /BYTE	Input	The pin for switching WORD mode and BYTE mode.	
		High level : WORD mode (1M-word by 16-bit)	
		Low level : BYTE mode (2M-word by 8-bit)	
A0 to A19	Input	Address input pins.	
(Address inputs)		A0 to A19 are used differently in the WORD mode and the BYTE mode.	
		WORD mode (1M-word by 16-bit)	
		A0 to A19 are used as 20 bits address signals.	
		BYTE mode (2M-word by 8-bit)	
		A0 to A19 are used as the upper 20 bits of total 21 bits of address signal.	
		(The least significant bit (A–1) is combined to O15.)	
O0 to O7, O8 to O14	Output	Data output pins.	
(Data outputs)		O0 to O7, O8 to O14 are used differently in the WORD mode and the BYTE mode.	
		WORD mode (1M-word by 16-bit)	
		The lower 15 bits of 16 bits data outputs to O0 to O14.	
		(The most significant bit (O15) combined to A–1.)	
		BYTE mode (2M-word by 8-bit)	
		8 bits data outputs to O0 to O7 and also O8 to O14 are high impedance.	
O15, A–1	Output, Input	O15, A–1 are used differently in the WORD mode and the BYTE mode.	
(Data output 15,		WORD mode (1M-word by 16-bit)	
LSB Address input)		The most significant output data bus (O15).	
		BYTE mode (2M-word by 8-bit)	
		The least significant address bus (A–1).	
/CE	Input	Chip activating signal.	
(Chip Enable)		When the OE is active, output states are following.	
		High level : High-Z	
		Low level : Data out	
/OE or OE or DC	Input	Output enable signal. The active level of OE is mask option. The active level of OE	
(Output Enable, Don't care)		can be selected from high active, low active and Don't care at order.	
Vcc	_	Supply voltage	
GND	-	Ground	
NC	_	Not internally connected. (The signal can be connected.)	

Block Diagram



Mask Option

The active levels of output enable pin (/OE or OE or DC) are mask programmable and optional, and can be selected from among " 0 " " 1 " " x " shown in the table below.

Option	/OE or OE or DC	OE active level
0	/OE	L
1	OE	Н
x	DC	Don't care

Operation modes for each option are shown in the tables below.

Operation mode (Option : 0)

/CE	/OE	Mode	Output state
L	L	Active	Data out
	Н		High-Z
Н	H or L	Standby	High-Z

Operation mode (Option : 1)

/CE	OE	Mode	Output state
L	L	Active	High-Z
	Н		Data out
Н	H or L	Standby	High-Z

Operation mode (Option : x)

/CE	DC	Mode	Output state
L	H or L	Active	Data out
Н	H or L	Standby	High-Z

Remark L: Low level input

H : High level input

Electrical Specifications

Absolute Maximum Ratings

Parameter	Symbol	Condition	Rating	Unit
Supply voltage	Vcc		–0.3 to +4.6	V
Input voltage	Vı		–0.3 to Vcc+0.3	V
Output voltage	Vo		–0.3 to Vcc+0.3	V
Operating ambient temperature	TA		-10 to +70	°C
Storage temperature	Tstg		–65 to +150	°C

Caution Exposing the device to stress above those listed in Absolute Maximum Ratings could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

Capacitance (TA = 25 °C)

Parameter	Symbol	Test condition	MIN.	TYP.	MAX.	Unit
Input capacitance	Сі	f = 1 MHz			10	pF
Output capacitance	Co				12	pF

DC Characteristics (TA = -10 to +70 °C, Vcc = 2.7 to 3.6 V)

Parameter	Symbol	Test conditions		MIN.	TYP.	MAX.	Unit
High level input voltage	Vін			2.0		Vcc + 0.3	V
Low level input voltage	VIL	V_{CC} = 3.0 V ± 0.3 V		-0.3		+0.5	V
		V_{CC} = 3.3 V \pm 0.3 V		-0.5		+0.8	
High level output voltage	Vон	Іон = –100 <i>µ</i> А		2.4			V
Low level output voltage	Vol	lo∟ = 2.1 mA				0.4	V
Input leakage current	lu	VI = 0 V to Vcc		-10		+10	μA
Output leakage current	Ilo	$V_{\rm O}$ = 0 V to V _{CC} , Chip des	elected	-10		+10	μA
Power supply current	Icc1	/CE = VIL (Active mode),	/CE = V _{IL} (Active mode), μ PD23C16340			40	mA
		lo = 0 mA μPD23C16380				55	
Standby current	Іссз	/CE = $V_{CC} - 0.2 V$ (Stand	by mode)			30	μA

AC Characteristics (TA = -10 to +70 °C, Vcc = 2.7 to 3.6 V)

	Parameter	Symbol	Test condition	V_{CC} = 3.0 V \pm 0.3 V		0.3 V	V_{CC} = 3.3 V \pm 0.3 V			Unit
				MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
	Address access time	tacc				90			85	ns
	Page access time	t PAC				25			25	ns
★	Address skew time	t skew	Note			10			10	ns
	Chip enable access time	t _{CE}				90			85	ns
	Output enable access time	toe				25			25	ns
	Output hold time	tон		0			0			ns
	Output disable time	t DF		0		25	0		25	ns
	WORD, /BYTE access time	twв				90			85	ns

* Note tskew indicates the following three types of time depending on the condition.

1) When switching /CE from high level to low level, t_{SKEW} is the time from the /CE low level input point until the next address is determined.

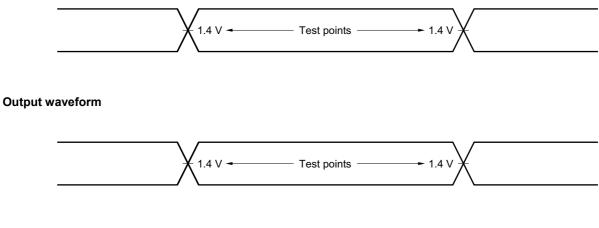
- 2) When switching /CE from low level to high level, tskew is the time from the address change start point to the /CE high level input point.
- 3) When /CE is fixed to low level, tskew is the time from the address change start point until the next address is determined.

Since specs are defined for tskew only when /CE is active, tskew is not subject to limitations when /CE is switched from high level to low level following address determination, or when the address is changed after /CE is switched from low level to high level.

Remark toF is the time from inactivation of Chip Enable input (/CE) or Output Enable input (/OE or OE) to high impedance state output.

AC Test Conditions

Input waveform (Rise / Fall time ≤ 5 ns)



Output load

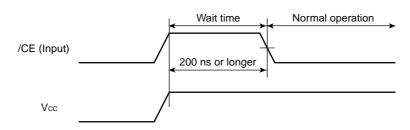
1TTL + 100 pF

★ Cautions on power application

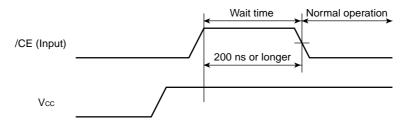
To ensure normal operation, always apply power using /CE following the procedure shown below.

- 1) Input a high level to /CE during and after power application.
- 2) Hold the high level input to /CE for 200 ns or longer (wait time).
- 3) Start normal operation after the wait time has elapsed.

Power Application Timing Chart 1 (When /CE is made high at power application)

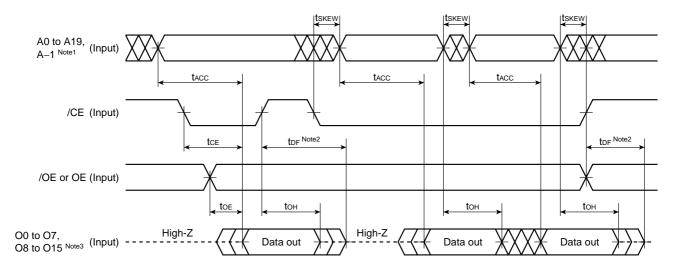


Power Application Timing Chart 2 (When /CE is made high after power application)



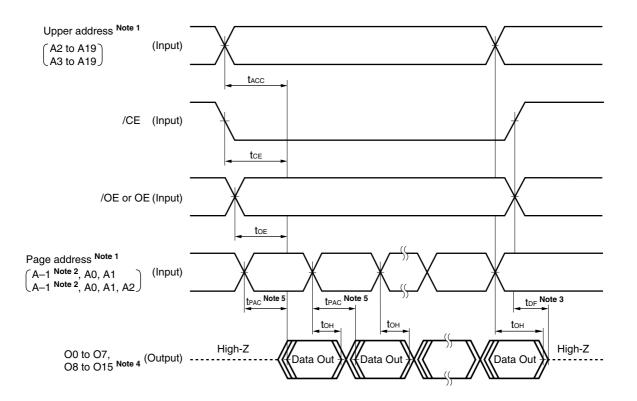
Caution Other signals can be either high or low during the wait time.

★ Read Cycle Timing Chart 1



- Notes 1. During WORD mode, A-1 is O15.
 - 2. tDF is the time from inactivation of Chip Enable input (/CE) or Output Enable input (/OE or OE) to high impedance state output.
 - 3. During BYTE mode, O8 to O14 are high impedance and O15 is A-1.

Read Cycle Timing Chart 2 (Page Access Mode)



Notes 1. The address differs depending on the product as follows.

Part Number	Upper address	Page address
μPD23C16340	A2 to A19	A–1, A0, A1
μPD23C16380	A3 to A19	A–1, A0, A1, A2

- **2.** During WORD mode, A–1 is O15.
- **3.** tDF is the time from inactivation of Chip Enable input (/CE) or Output Enable input (/OE or OE) to high impedance state output.
- 4. During BYTE mode, O8 to O14 are high impedance and O15 is A-1.
- **5.** The definition of page access time is as follows.

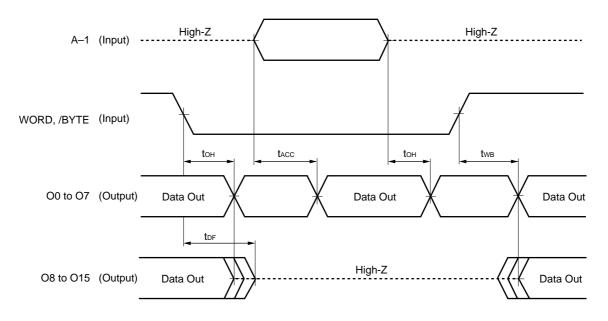
[µPD23C16340]

Page access time	Upper address (A2 to A19)	/CE input condition	/OE or OE input condition
	inputs condition		
t pac	Before tacc - tPAC	Before tce - tpac	Before stabilizing of page
			address (A-1, A0, A1)

[µPD23C16380]

Page access time	Upper address (A3 to A19)	/CE input condition	/OE or OE input condition
	inputs condition		
t PAC	Before tacc – tPAC	Before t _{CE} - t _{PAC}	Before stabilizing of page
			address (A-1, A0, A1, A2)

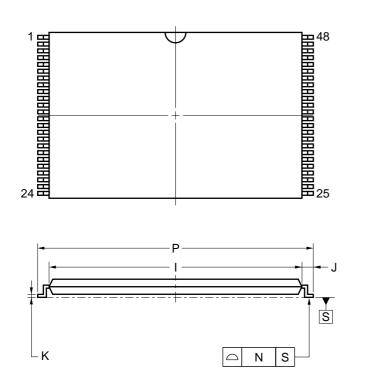
WORD, /BYTE Switch Timing Chart

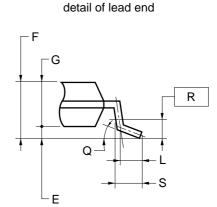


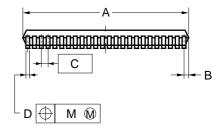
Remark Chip Enable (/CE) and Output Enable (/OE or OE) : Active.

Package Drawings

48-PIN PLASTIC TSOP (I) (12x20)





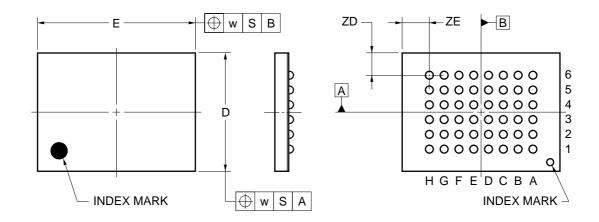


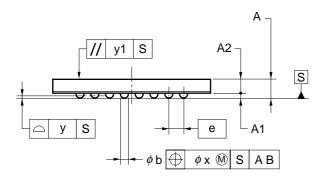
NOTES

- 1) Each lead centerline is located within 0.10 mm of its true position (T.P.) at maximum material condition.
- 2) "A" excludes mold flash. (Includes mold flash : 12.4 mm MAX.)

ITEM	MULIMETEDO
ITEM	MILLIMETERS
A	12.0±0.1
В	0.45 MAX.
С	0.5 (T.P.)
D	0.22±0.05
E	0.1±0.05
F	1.2 MAX.
G	1.0±0.05
I	18.4±0.1
J	0.8±0.2
к	0.145±0.05
L	0.5
М	0.10
Ν	0.10
Р	20.0±0.2
Q	3°+5° -3°
R	0.25
S	0.60±0.15
	S48GZ-50-MJH-1

* 48-PIN TAPE FBGA(8x6)





ITEM	MILLIMETERS
D	6.0±0.1
E	8.0±0.1
w	0.2
е	0.80
Α	0.97±0.10
A1	0.27±0.05
A2	0.70
b	0.45±0.05
x	0.08
У	0.1
y1	0.2
ZD	1.00
ZE	1.20
	P48F9-80-BC3

Recommended Soldering Conditions

Please consult with our sales offices for soldering conditions of the μ PD23C16340 and μ PD23C16380.

Types of Surface Mount Device

 μPD23C16340GZ-MJH
 : 48-pin PLASTIC TSOP(I) (12 x 20) (Normal bent)

 μPD23C16340F9-BC3
 : 48-pin TAPE FBGA (8 x 6)

 μPD23C16380GZ-MJH
 : 48-pin PLASTIC TSOP(I) (12 x 20) (Normal bent)

 μPD23C16380F9-BC3
 : 48-pin TAPE FBGA (8 x 6)

Revision History

Edition/	Page		Type of	Location	Description
Date	This	Previous	revision		(Previous edition \rightarrow This edition)
	edition	edition			
2nd edition/	Throughout	Throughout	Modification		Preliminary Data Sheet \rightarrow Data Sheet
Feb. 2003	p.9	p.9	Addition	AC Characteristics	Address skew time (tskew)
					Note
	p.10	-	Addition		Cautions on power application
	p.11	p.10	Modification		Read Cycle Timing Chart 1
	p.15	p.14	Modification	Package Drawings	Preliminary version \rightarrow Standard version

- NOTES FOR CMOS DEVICES —

① PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note:

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

(2) HANDLING OF THE APPLIED WAVEFORM OF INPUT PINS AND THE UNUSED INPUT PINS FOR CMOS

Note:

Input levels of CMOS devices must be fixed. CMOS devices behave differently than Bipolar or NMOS devices. If the input of a CMOS device stays in an area that is between V_{IL} (MAX.) and V_{IH} (MIN.) due to the effects of noise or some other irregularity, malfunction may result. Therefore, not only the input waveform is fixed, but also the waveform changes, it is important to use the CMOS device under AC test conditions. For unused input pins in particular, CMOS devices should not be operated in a state where nothing is connected, so input levels of CMOS devices must be fixed to high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to V_{DD} or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

③ STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note:

Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

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